

**2N4013**  
**2N4014**

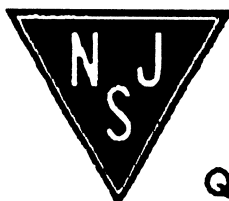
**TO-18 (TO-206AA)**  
**SWITCHING TRANSISTOR**  
 NPN SILICON

**MAXIMUM RATINGS**

Rating	Symbol	2N4013	2N4014	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	30	50	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	50	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0		Vdc
Collector Current — Continuous	I <sub>C</sub>	1.0		Adc
— Peak		2.0		
Total Device Dissipation (i <sub>C</sub> T <sub>A</sub> = 25°C)	P <sub>D</sub>	0.5		Watt
Derate above 25°C		28.6		mW/°C
Total Device Dissipation (i <sub>C</sub> T <sub>C</sub> = 25°C)	P <sub>D</sub>	1.4		Watts
Derate above 25°C		6.8		mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50 30	— —	— —	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 μAdc, V <sub>BE</sub> = 0)	V <sub>(BR)CES</sub>	80 50	— —	— —	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	80 50	— —	— —	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	—	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	—	0.12	1.7	μAdc
(V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0)		—	0.12	1.7	
(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C)		—	—	120	
(V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C)		—	—	120	
Collector Cutoff Current (V <sub>CE</sub> = 80 Vdc, V <sub>EB</sub> = 0)	I <sub>CES</sub>	—	0.15	10	μAdc
(V <sub>CE</sub> = 50 Vdc, V <sub>EB</sub> = 0)		—	0.15	10	
<b>ON CHARACTERISTICS(1)</b>					
DC Current Gain (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc)	h <sub>FE</sub>	30	—	—	—
(I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)		60	—	150	
(I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc, T <sub>A</sub> = -55°C)		30	—	—	
(I <sub>C</sub> = 300 mAdc, V <sub>CE</sub> = 1.0 Vdc)		40	—	—	
(I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 1.0 Vdc)		35	—	—	
(I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 1.0 Vdc, T <sub>A</sub> = -55°C)		20	—	—	
(I <sub>C</sub> = 800 mAdc, V <sub>CE</sub> = 2.0 Vdc)		20	—	—	
	2N4014	20	—	—	
	2N4013	25	—	—	
(I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc)		25	—	—	
	2N4014	30	—	—	
	2N4013	30	—	—	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)	V <sub>CE(sat)</sub>	—	0.17	0.25	Vdc
	2N4014	—	0.17	0.25	
	2N4013	—	0.17	0.25	
(I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)		—	0.19	0.26	
	2N4014	—	0.19	0.26	
	2N4013	—	0.19	0.20	



**2N4013, 2N4014**

**ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
$(I_C = 300 \text{ mAdc}, I_B = 30 \text{ mAdc})$	2N4014	—	0.25	0.40	
	2N4013	—	0.25	0.32	
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	2N4014	—	0.30	0.52	
	2N4013	—	0.30	0.42	
$(I_C = 800 \text{ mAdc}, I_B = 80 \text{ mAdc})$	2N4014	—	0.43	0.80	
	2N4013	—	0.43	0.65	
$(I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc})$	2N4014	—	0.55	0.95	
	2N4013	—	0.55	0.75	
Base-Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc})$ $(I_C = 300 \text{ mAdc}, I_B = 30 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$ $(I_C = 800 \text{ mAdc}, I_B = 80 \text{ mAdc})$ $(I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc})$	$V_{BE(sat)}$	—	—	0.76	Vdc
		—	—	0.86	
		—	—	1.1	
		0.8	—	1.1	
		—	—	1.5	
		—	—	1.7	

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain — Bandwidth Product(2) $(I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz})$	$f_T$	300	—	—	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	$C_{obo}$	2N4014	—	10	pF
		2N4013	—	12	
Input Capacitance $(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	$C_{ibo}$	—	—	55	pF

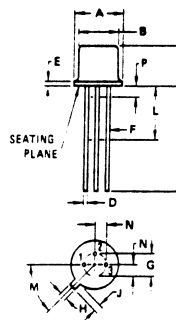
**SWITCHING CHARACTERISTICS**

Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = 3.8 \text{ Vdc}, I_C = 500 \text{ mAdc}, I_{B1} = 50 \text{ mAdc})$ (Figures 8, 10)	2N4014 2N4013	$t_d$	—	5.0	10	ns
Rise Time			$t_r$	—	15	30	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_C = 500 \text{ mAdc}, I_{B1} = I_{B2} = 50 \text{ mAdc})$ (Figures 9, 10)	2N4014 2N4013	$t_s$	—	30	50	ns
Fall Time			$t_f$	—	20 25	25 30	ns
Turn-On Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = 3.8 \text{ Vdc}, I_C = 500 \text{ mAdc}, I_{B1} = 50 \text{ mAdc})$ (Figures 8, 10)		$t_{on}$	—	20	35	ns
Turn-Off Time	$(V_{CC} = 30 \text{ Vdc}, I_C = 500 \text{ mAdc}, I_{B1} = I_{B2} = 50 \text{ mAdc})$ (Figures 9, 10)	2N4014 2N4013	$t_{off}$	—	50	60	ns

(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 1.0%.

(2)  $f_T = h_{fe1} \cdot f_{test}$ .

TO-18 (TO-206AA)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.406	0.533	0.016	0.021
E	—	0.762	—	0.030
F	0.406	0.483	0.016	0.019
G	2.54 BSC	—	0.100 BSC	—
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	4.50 BSC	—	0.175 BSC	—
N	1.27 BSC	—	0.050 BSC	—
P	—	1.27	—	0.050